

650V 30A Field Stop Trench IGBT

V _{CES}	650V
I _{C(100°C)}	30A
V _{CE(sat) (Typ.)}	1.65V
P_D	194W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Low Switching Loss
- 3) Short Circuit Withstand Time 5µs
- 4) Built in Very Fast & Soft Recovery FRD (RFN Series)
- 5) Pb free Lead Plating; RoHS Compliant

Applications

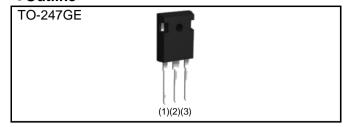
General Inverter

UPS

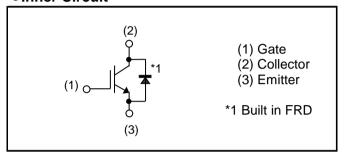
Power Conditioner

Welder

Outline



•Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	600
	Packing code	C13
	Marking	RGT60TS65D

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	55	А
Collector Current	T _C = 100°C	I _C	30	А
Pulsed Collector Current		I _{CP} *1 90		А
Diode Forward Current	T _C = 25°C	I _F	40	А
	T _C = 100°C	I _F	20	А
Diode Pulsed Forward Current		I _{FP} *1 90		А
Dower Dissipation	T _C = 25°C	P _D	194	W
Power Dissipation	T _C = 100°C	P _D	97	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Linit
Farameter		Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.77	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	2.00	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_C = 10 \mu A, V_{GE} = 0 V$	650	1	-	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	-	-	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, \ V_{CE} = 0V$	-	•	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 21.0 \text{mA}$	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_C = 30A$, $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.65 2.15	2.1 -	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Darameter	Symbol	Conditions		Unit		
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Input Capacitance	C _{ies}	V _{CE} = 30V	-	1730	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	72	-	pF
Reverse Transfer Capacitance	C_{res}	f = 1MHz	-	29	-	
Total Gate Charge	Q_g	V _{CE} = 300V	-	58	-	
Gate - Emitter Charge	Q_ge	$I_C = 30A$	-	15	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	20	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 30A, V_{CC} = 400V$	-	29	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	40	-	ns
Turn - off Delay Time	$t_{d(off)}$	T _j = 25°C	-	100	-	
Fall Time	t _f	Inductive Load	-	60	-	
Turn - on Delay Time	t _{d(on)}	$I_C = 30A, V_{CC} = 400V$	-	29	-	
Rise Time	t _r	$V_{GE} = 15V, R_{G} = 10\Omega$	-	41	-	200
Turn - off Delay Time	$t_{d(off)}$	T _j = 175°C	-	113	-	ns
Fall Time	t _f	Inductive Load	-	105	-	
		$I_C = 90A, V_{CC} = 520V$				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650 V, V_{GE} = 15 V$	FU	LL SQUA	RE	-
		$R_G = 50\Omega, T_j = 175^{\circ}C$				
		$V_{CC} \le 360V$				
Short Circuit Withstand Time	t_{sc}	V _{GE} = 15V	5	-	-	μs
		T _j = 25°C				

●FRD Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Unit
Diode Forward Voltage	V _F	$I_F = 20A$ $T_j = 25$ °C $T_j = 175$ °C	-	1.35 1.15	1.8	V
Diode Reverse Recovery Time	t _{rr}	$I_F = 20A$ $V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 25^{\circ}C$	-	58	-	ns
Diode Peak Reverse Recovery Current	I _{rr}		-	6.5	-	А
Diode Reverse Recovery Charge	Q_{rr}		-	0.21	-	μC
Diode Reverse Recovery Time	t _{rr}	I _F = 20A	-	236	-	ns
Diode Peak Reverse Recovery Current	I _{rr}	$V_{CC} = 400V$ $di_F/dt = 200A/\mu s$ $T_j = 175^{\circ}C$	-	10.7	-	А
Diode Reverse Recovery Charge	Q_{rr}		-	1.36	-	μC

Fig.1 Power Dissipation vs. Case Temperature

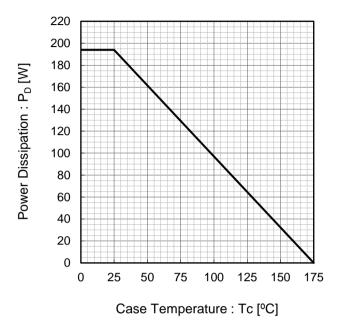


Fig.2 Collector Current vs. Case Temperature

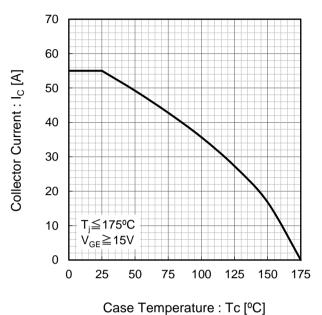
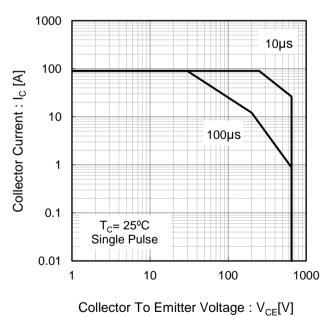
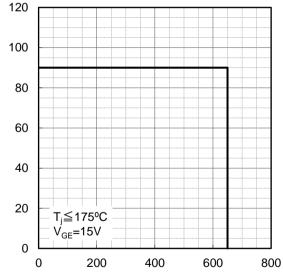


Fig.3 Forward Bias Safe Operating Area



Collector Current : I_C [A]

Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.5 Typical Output Characteristics

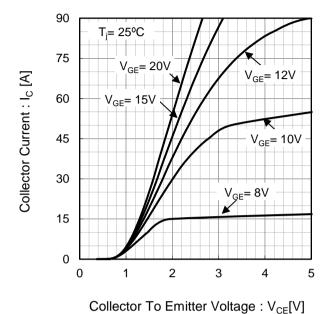
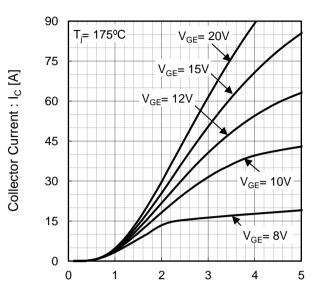


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : $V_{CE}[V]$

Fig.7 Typical Transfer Characteristics

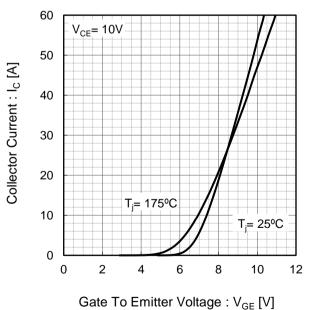
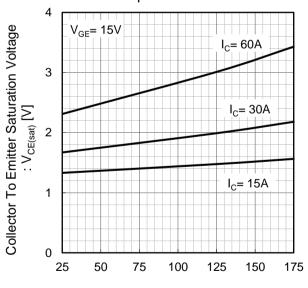
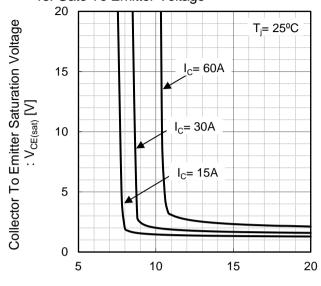


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



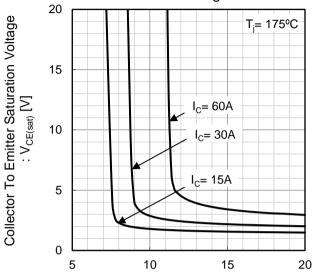
Junction Temperature : T_i [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage: V_{GE} [V]

Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage: V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current

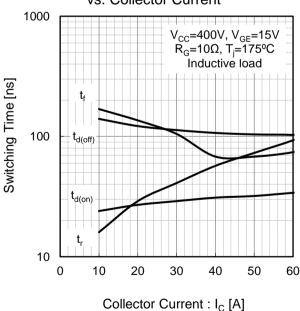
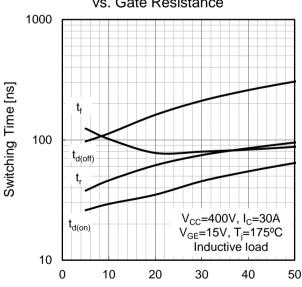


Fig.12 Typical Switching Time vs. Gate Resistance



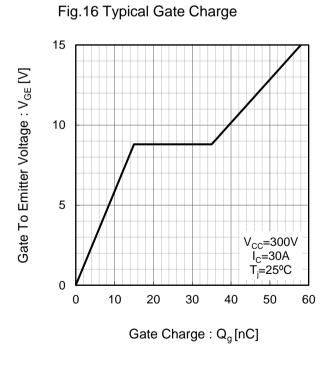
Gate Resistance : $R_G[\Omega]$

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1 $\mathsf{E}_{\mathsf{off}}$ 0.1 V_{CC} =400V, V_{GE} =15V R_{G} =10 Ω , T_{j} =175°C Inductive load 0.01 0 10 20 30 40 50 60 Collector Current : I_C [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] $\mathsf{E}_{\mathsf{off}}$ 1 E_{on} 0.1 V_{CC}=400V, I_C=30A V_{GE}=15V, T_j=175°C Inductive load 0.01 0 20 30 40 50 10 Gate Resistance : $R_G[\Omega]$

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz V_{GE}=0V T_i=25°C 1 0.01 0.1 10 100 Collector To Emitter Voltage : $V_{CE}[V]$



0

0.5

•Electrical Characteristic Curves

Fig.17 Typical Diode Forward Current

Forward Voltage : V_F[V]

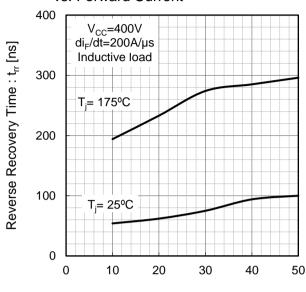
1.5

2

2.5

3

Fig.18 Typical Diode Reverse Recovery Time vs. Forward Current



Forward Current : I_F [A]

Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current

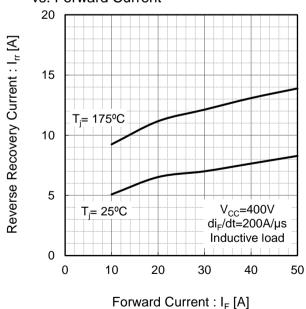
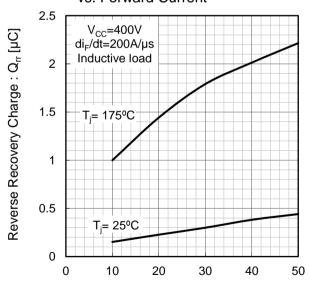


Fig.20 Typical Diode Reverse Recovery Charge vs. Forward Current



Forward Current : I_F [A]

Fig.21 IGBT Transient Thermal Impedance

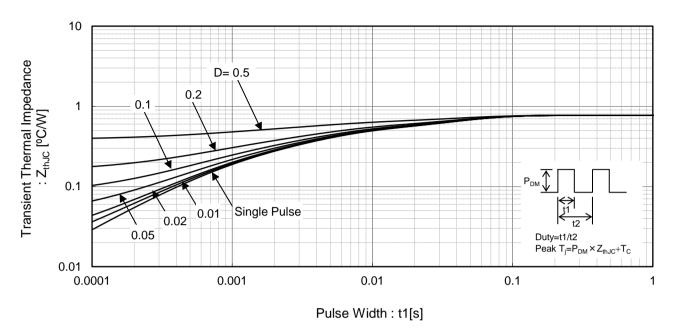
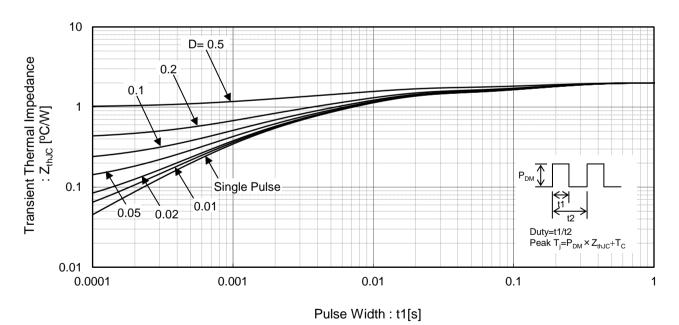


Fig.22 Diode Transient Thermal Impedance



●Inductive Load Switching Circuit and Waveform

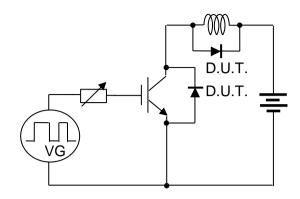


Fig.23 Inductive Load Circuit

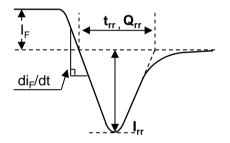


Fig.25 Diode Reverce Recovery Waveform

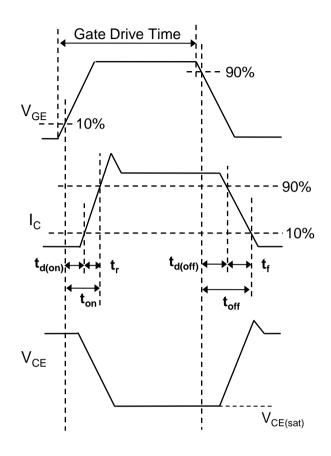


Fig.24 Inductive Load Waveform

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